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(71) Applicant *(for all designated States except US)*: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **PELELLA, Mario, M.** [US/US]; 1876 Miramonte Avenue, Mountain View, CA 94040 (US). **WU, Donggang, D.** [US/US]; 10222 Dianella Lane, Austin, TX 78759 (US). **BULLER, James, F.** [US/US]; 6908 India Cove, Austin, TX 78759 (US).

(74) Agent: **DRAKE, Paul, S.**; Advanced Micro Devices, Inc., 5204 East Ben White Boulevard, Mail Stop 562, Austin, TX 78741 (US).

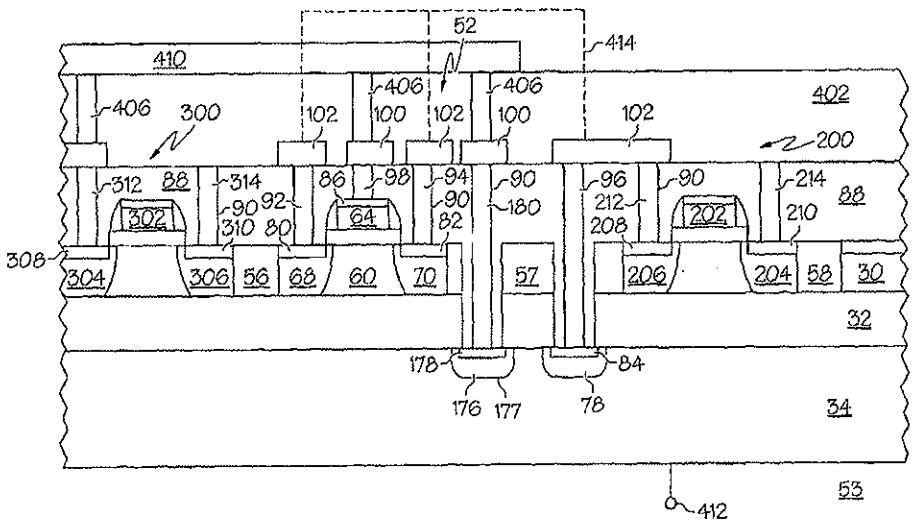
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(54) Title: SOI DEVICE AND METHOD FOR ITS FABRICATION



(57) Abstract: A silicon on insulator (SOI) device [53] and methods for fabricating such a device are provided. The device includes an MOS capacitor [52] coupled between voltage busses [100, 102] and formed in a monocrystalline semiconductor layer [30] overlying an insulator layer [32] and a semiconductor substrate [34]. The device includes at least one electrical discharge path [86, 98, 180, 178] for discharging potentially harmful charge build up on the MOS capacitor [52]. The MOS capacitor has a conductive electrode material forming a first plate [64] of the MOS capacitor and an impurity doped region [60] in the monocrystalline silicon layer [30] beneath the conductive electrode material forming a second plate. A first voltage bus [100] is coupled to the first plate [64] of the capacitor and to an electrical discharge path through a diode [177] formed in the semiconductor substrate and a second voltage bus [102] is coupled to the second plate [60] of the capacitor.

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